N- and P-Channel 20V (D-S) Power MOSFET

FEATURES

- Low $R_{DS(ON)}$ to minimize conductive losses
- Low gate charge for fast power switching
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Load Switch
- Power Management
- Portable Devices

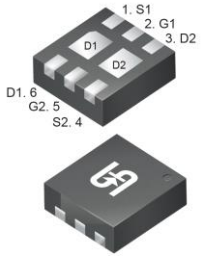
KEY PERFORMANCE PARAMETERS

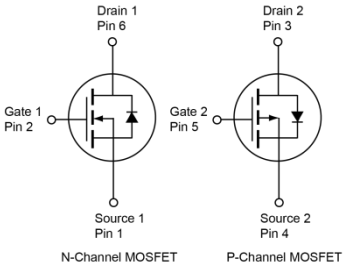
PARAMETER		TYPE	VALUE	UNIT
V_{DS}		N-ch	20	V
		P-ch	-20	
$R_{DS(on)}$ (max)	V_{GS} = 4.5V	N-ch	30	mΩ
	V_{GS} = 2.5V		36	
	V_{GS} = 1.8V		42	
	V_{GS} = -4.5V	P-ch	55	
	V_{GS} = -2.5V		78	
	V_{GS} = -1.8V		90	
Q_g		N-ch	9.1	nC
		P-ch	9.8	

Pb-Free

RoHS COMPLIANT HALOGEN FREE

TDFN22





Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

PARAMETER		SYMBOL	N-ch	P-ch	UNIT
Drain-Source Voltage		V_{DS}	20	-20	V
Gate-Source Voltage		V_{GS}	±12	±12	V
Continuous Drain Current (Note 1)	T_C = 25°C	I_D	11.6	-9	A
	T_A = 25°C		6.4	-5	
Pulsed Drain Current		I_{DM}	46.4	-36	A
Total Power Dissipation	T_C = 25°C	P_D	6.25	6.25	W
	T_C = 125°C		1.25	1.25	
Total Power Dissipation	T_A = 25°C	P_D	1.89	1.89	W
	T_A = 125°C		0.38	0.38	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150		°C

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Thermal Resistance – Junction to Case	$R_{\Theta JC}$	20	°C/W
Thermal Resistance – Junction to Ambient	$R_{\Theta JA}$	66	

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS (T_A = 25°C unless otherwise noted)							
PARAMETER	**CONDITIONS**	**SYMBOL**	**TYPE**	**MIN**	**TYP**	**MAX**	**UNIT**
Static							
Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	BV_{DSS}	N-ch	20	--	--	V
	V_{GS} = 0V, I_D = -250μA		P-ch	-20	--	--	
Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	$V_{GS(TH)}$	N-ch	0.5	0.8	1	V
	V_{GS} = V_{DS}, I_D = -250μA		P-ch	-0.45	-0.7	-1	
Gate-Source Leakage Current	V_{GS} = ±12V, V_{DS} = 0V	I_{GSS}	N-ch	--	--	±100	nA
	V_{GS} = ±12V, V_{DS} = 0V		P-ch	--	--	±100	
Drain-Source Leakage Current	V_{GS} = 0V, V_{DS} = 20V	I_{DSS}	N-ch	--	--	1	μA
	V_{GS} = 0V, V_{DS} = 20V T_J = 125°C			--	--	100	
	V_{GS} = 0V, V_{DS} = -20V		P-ch	--	--	-1	
	V_{GS} = 0V, V_{DS} = -20V T_J = 125°C			--	--	-100	
Drain-Source On-State Resistance (Note 2)	V_{GS} = 4.5V, I_D = 6.4A	$R_{DS(on)}$	N-ch	--	17	30	mΩ
	V_{GS} = 2.5V, I_D = 5.8A			--	22	36	
	V_{GS} = 1.8V, I_D = 5.4A			--	32	42	
	V_{GS} = -4.5V, I_D = -5A		P-ch	--	48	55	
	V_{GS} = -2.5V, I_D = -4.2A			--	60	78	
	V_{GS} = -1.8V, I_D = -3.9A			--	78	90	
Forward Transconductance (Note 2)	V_{DS} = 5V, I_D = 6.4A	g_{fs}	N-ch	--	28	--	S
	V_{DS} = -5V, I_D = -5A		P-ch	--	15	--	
Dynamic (Note 3)							
Total Gate Charge	N-ch V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6.4A P-ch V_{GS} = -4.5V, V_{DS} = -10V, I_D = -5A	Q_g	N-ch	--	9.1	--	nC
			P-ch	--	9.8	--	
Gate-Source Charge		Q_{gs}	N-ch	--	1.3	--	
			P-ch	--	1.1	--	
Gate-Drain Charge		Q_{gd}	N-ch	--	2.7	--	
			P-ch	--	2.7	--	
Input Capacitance	N-ch V_{GS} = 0V, V_{DS} = 10V f = 1.0MHz P-ch V_{GS} = 0V, V_{DS} = -10V f = 1.0MHz	C_{iss}	N-ch	--	677	--	pF
			P-ch	--	744	--	
Output Capacitance		C_{oss}	N-ch	--	120	--	
			P-ch	--	106	--	
Reverse Transfer Capacitance		C_{rss}	N-ch	--	89	--	
			P-ch	--	97	--	
Gate Resistance	f = 1.0MHz	R_g	N-ch	--	3	--	Ω
			P-ch	--	80	--	

ELECTRICAL SPECIFICATIONS (T_A = 25°C unless otherwise noted)							
PARAMETER	**CONDITIONS**	**SYMBOL**	**TYPE**	**MIN**	**TYP**	**MAX**	**UNIT**
Switching (Note 3)							
Turn-On Delay Time	N-ch V_{GS} = 4.5V, R_G = 2Ω V_{DS} = 10V, I_D = 6.4A P-ch V_{GS} = -4.5V, R_G = 2Ω V_{DS} = -10V, I_D = -5A	$t_{d(on)}$	N-ch	--	8	--	ns
			P-ch	--	10	--	
Turn-On Rise Time		t_r	N-ch	--	41	--	
			P-ch	--	34	--	
Turn-Off Delay Time		$t_{d(off)}$	N-ch	--	25	--	
			P-ch	--	69	--	
Turn-Off Fall Time		t_f	N-ch	--	30	--	
			P-ch	--	68	--	
Source-Drain Diode							
Forward Voltage (Note 2)	V_{GS} = 0V, I_S = 6.4A	V_{SD}	N-ch	--	0.7	--	V
	V_{GS} = 0V, I_S = -5A		P-ch	--	-0.8	--	
Reverse recovery Time	N-ch I_S= 6.4A, dI/dt=100A/μs P-ch I_S= -5A, dI/dt=100A/μs	t_{rr}	N-ch		22		nc
			P-ch		113		
Reverse Recovery Charge		Q_{rr}	N-ch	--	6		nc
			P-ch	--	160		

Notes:

1. Silicon limited current only.
2. Pulse test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.
3. Switching time is essentially independent of operating temperature.

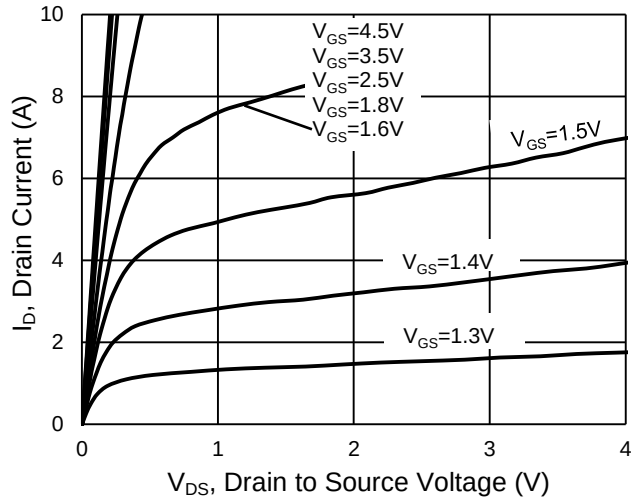
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM2537CQ RFG	TDFN22	3,000pcs / 7” Reel

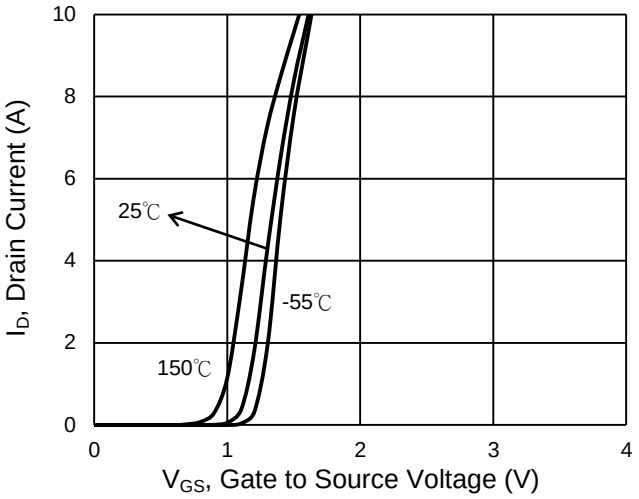
CHARACTERISTICS CURVES (N-Channel)

(T_A = 25°C unless otherwise noted)

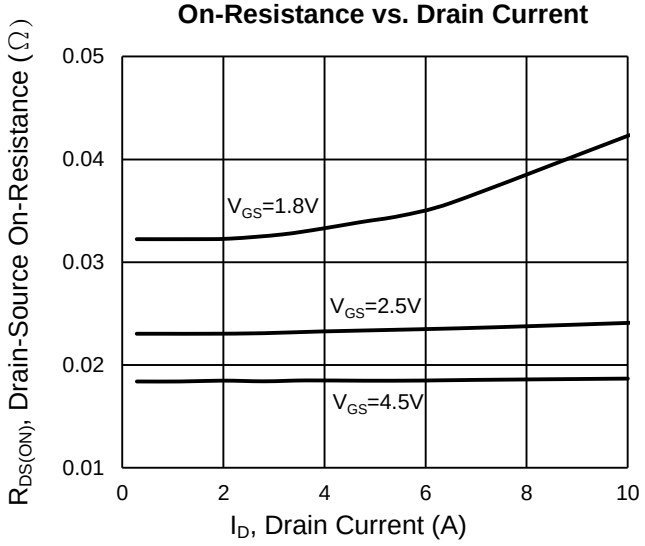
Output Characteristics



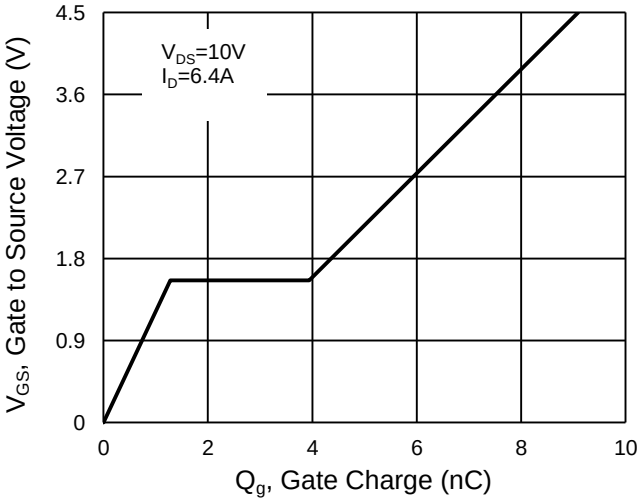
Transfer Characteristics



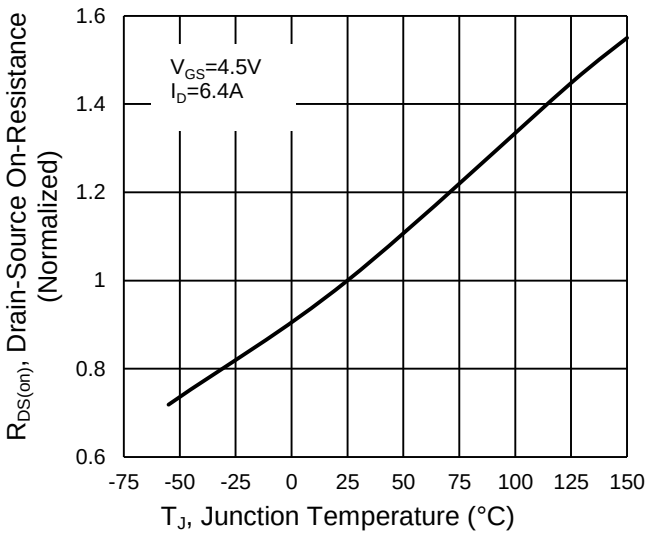
On-Resistance vs. Drain Current



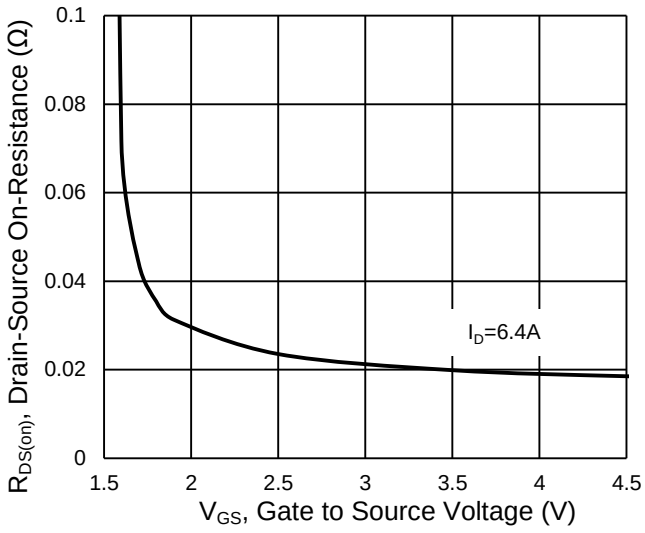
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



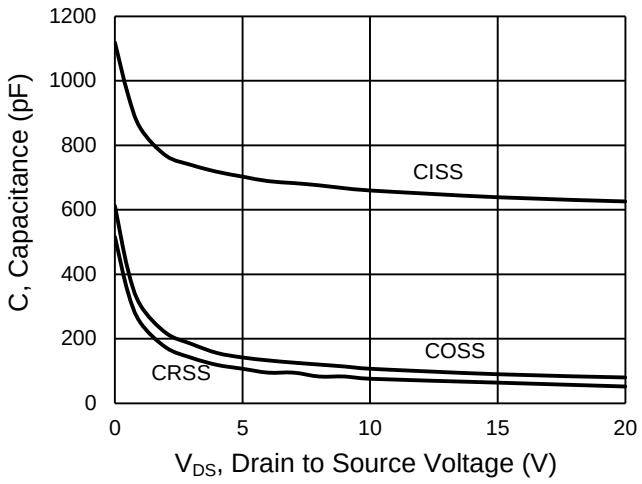
On-Resistance vs. Gate-Source Voltage



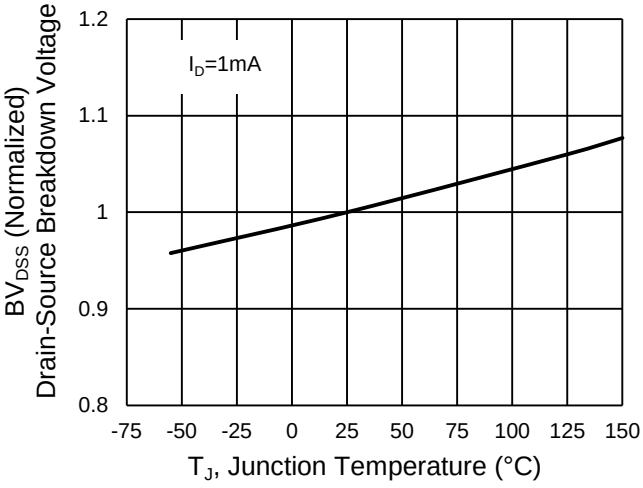
CHARACTERISTICS CURVES (N-Channel)

(T_A = 25°C unless otherwise noted)

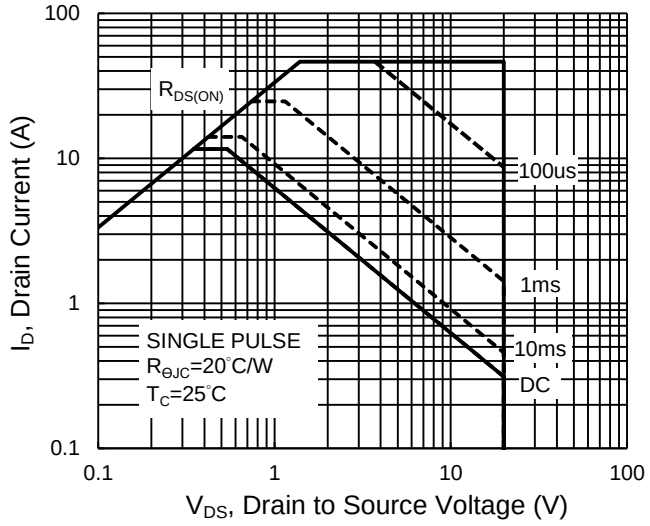
Capacitance vs. Drain-Source Voltage



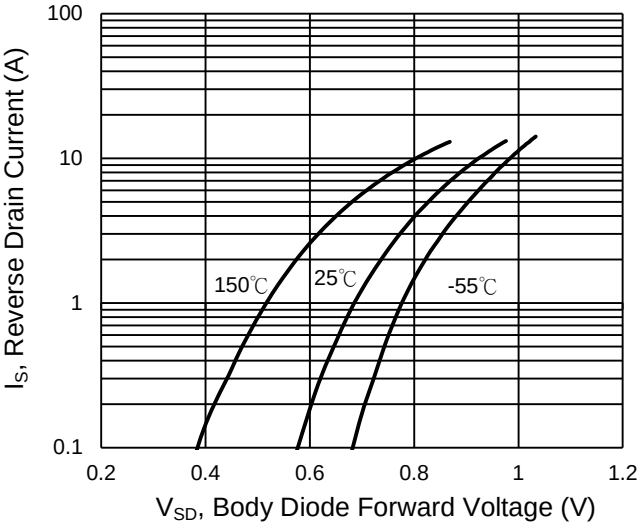
BV_{DSS} vs. Junction Temperature



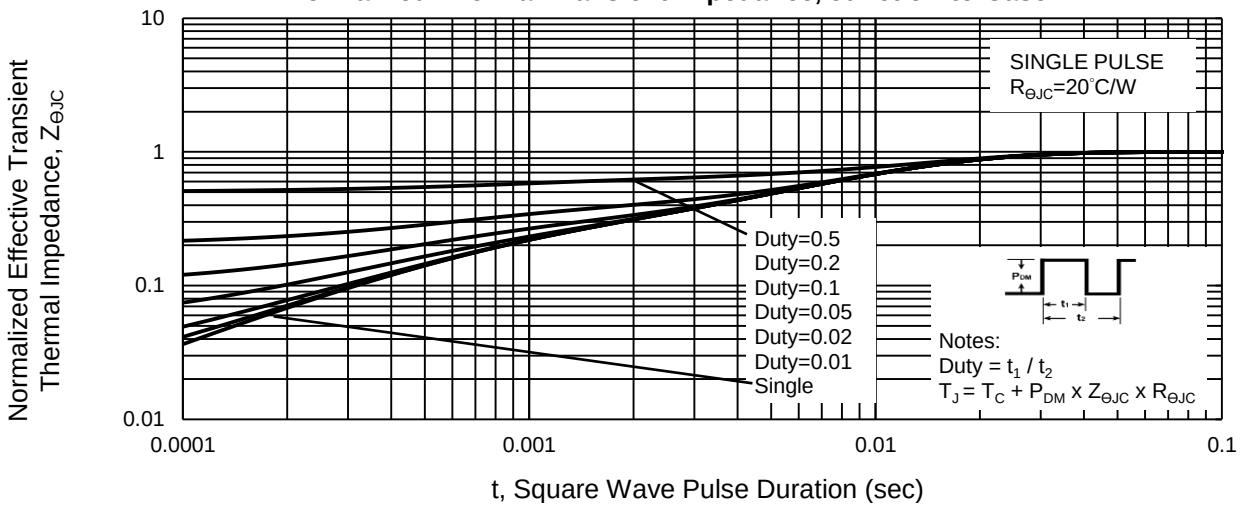
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage



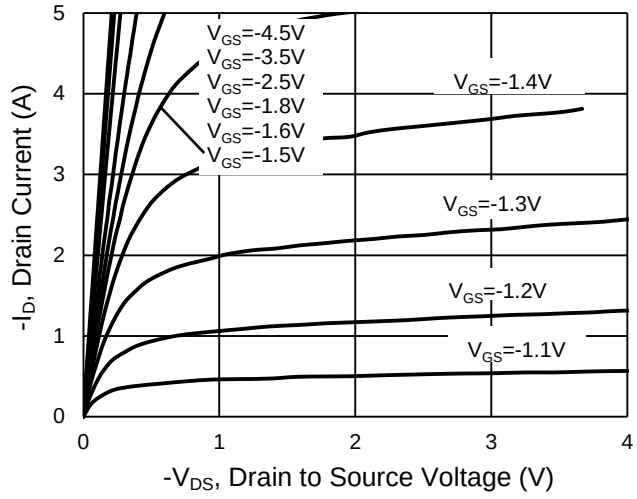
Normalized Thermal Transient Impedance, Junction-to-Case



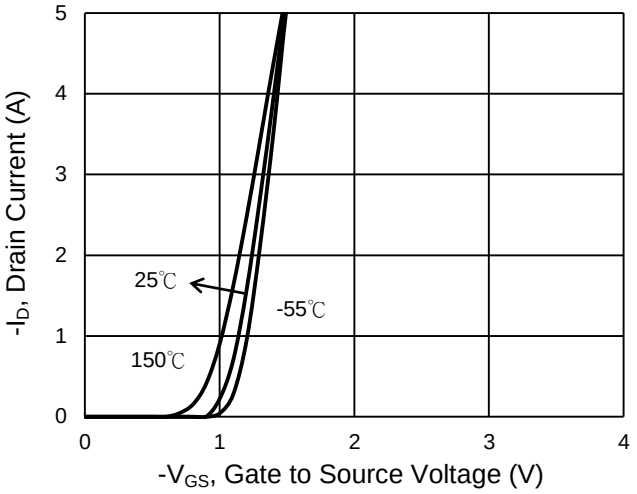
CHARACTERISTICS CURVES (P-Channel)

(T_A = 25°C unless otherwise noted)

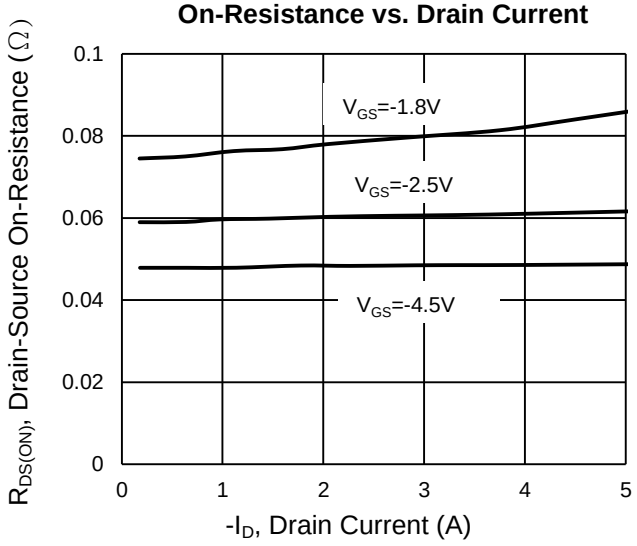
Output Characteristics



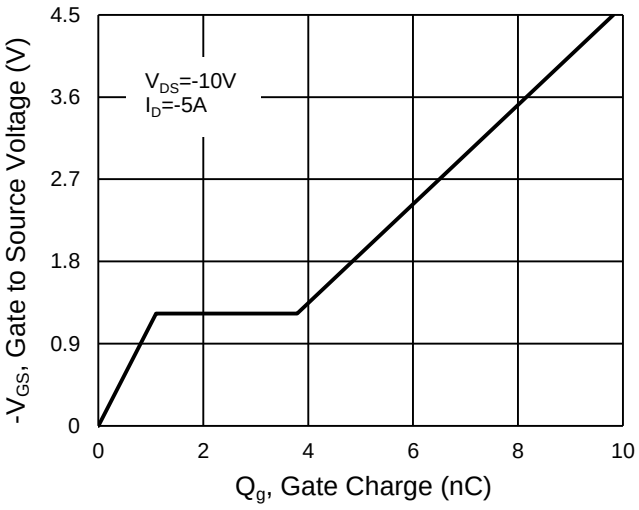
Transfer Characteristics



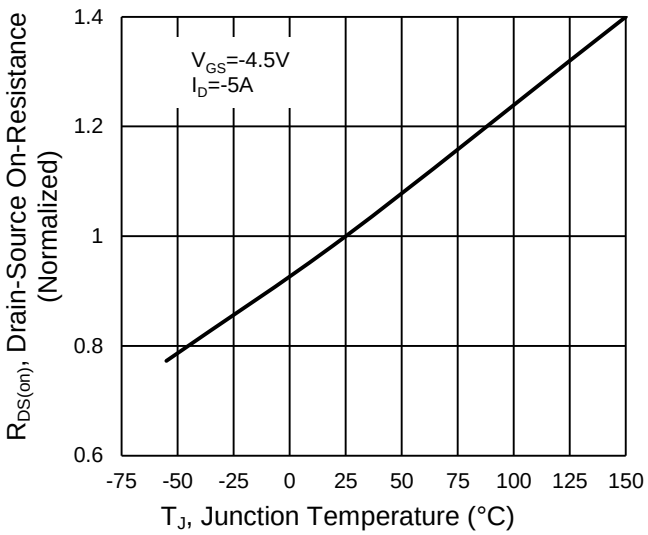
On-Resistance vs. Drain Current



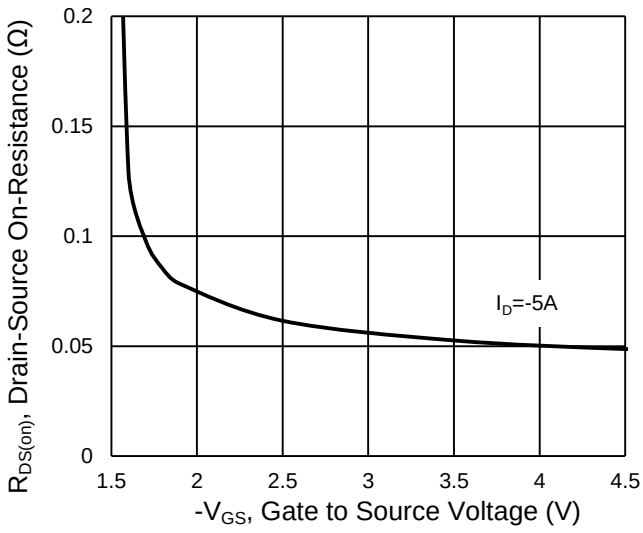
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



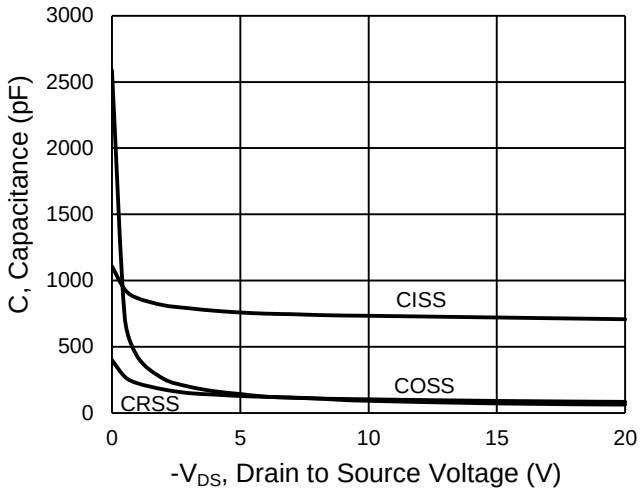
On-Resistance vs. Gate-Source Voltage



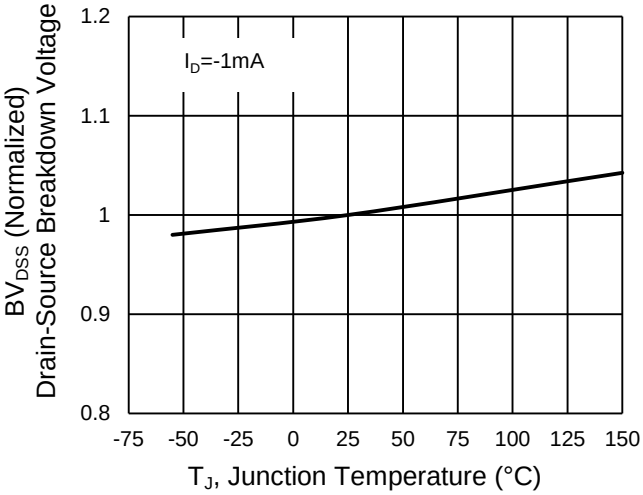
CHARACTERISTICS CURVES (P-Channel)

(T_A = 25°C unless otherwise noted)

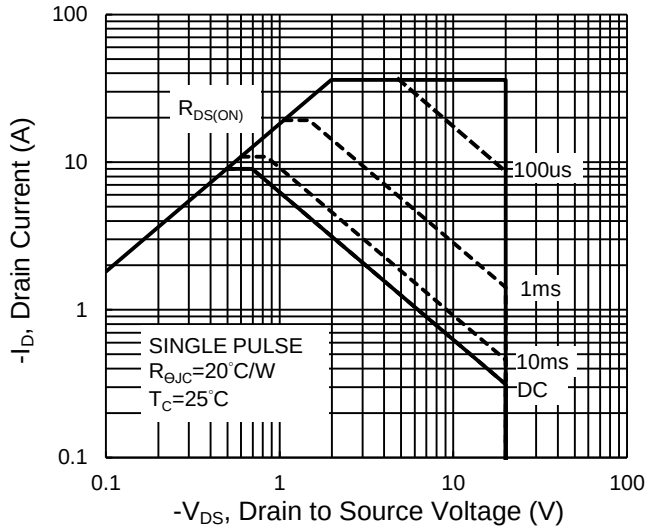
Capacitance vs. Drain-Source Voltage



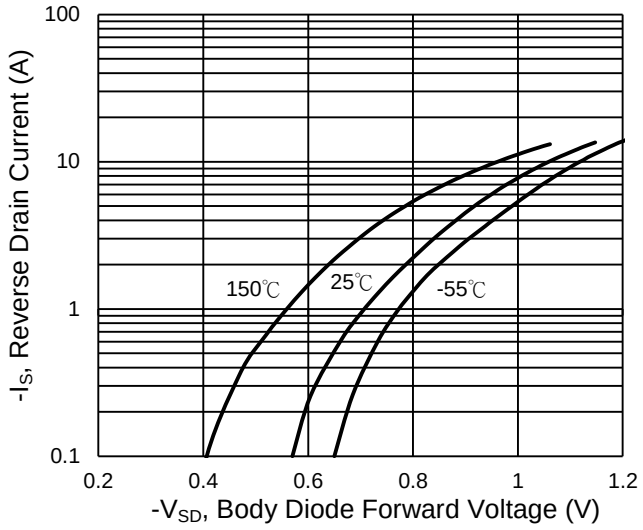
BV_{DSS} vs. Junction Temperature



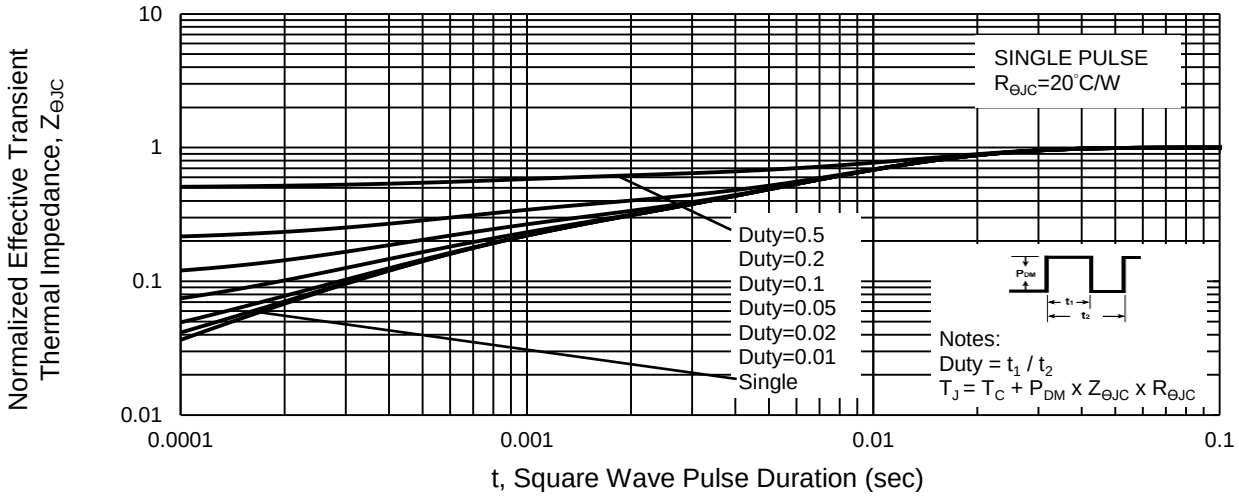
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

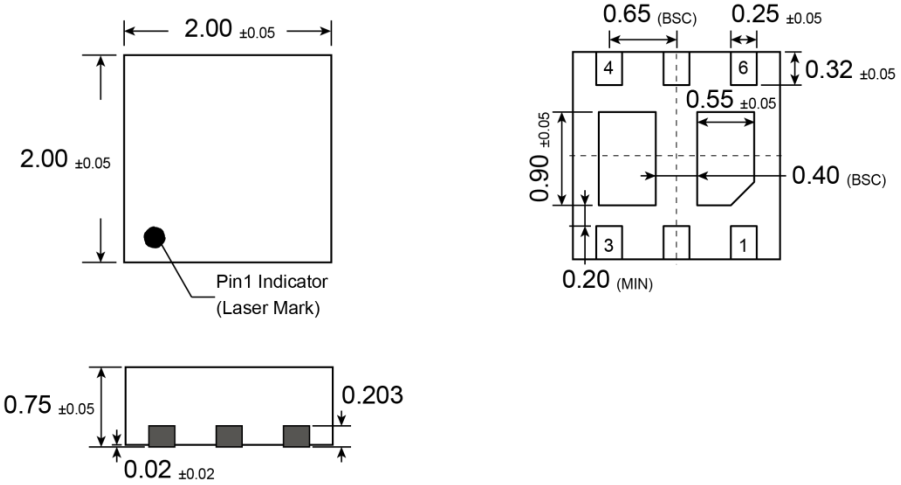


Normalized Thermal Transient Impedance, Junction-to-Case

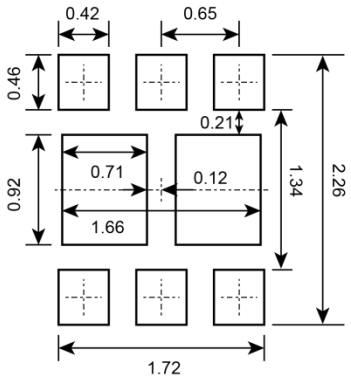


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

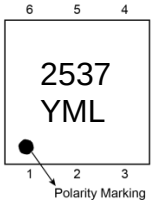
TDFN22



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free

O	=Jan	**P**	=Feb	**Q**	=Mar	**R**	=Apr
S	=May	**T**	=Jun	**U**	=Jul	**V**	=Aug
W	=Sep	**X**	=Oct	**Y**	=Nov	**Z**	=Dec

L = Lot Code (1~9, A~Z)

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- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

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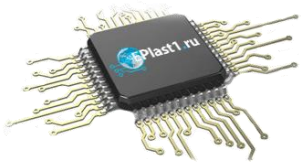
- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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